■ DESCRIPTION

●ELECTRONIC BALLAST

●ELECTRONIC TRANSFORMER

●SWITCH MODE POWER SUPPLY

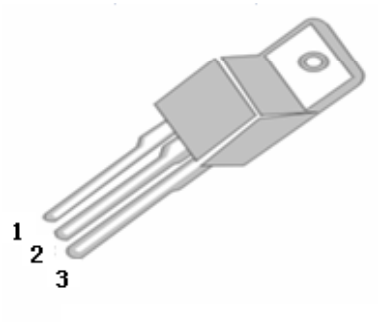
■ FEATURES:

●LOW THERMAL RESISTANCE ●HIGH INPUT RESISTANCE ●FAST SWITCHING ●ROHS COMPLIANT

■ MAXIMUM RATINGS (Tc=25℃)

PARAMETER	SYMBOL	VALUE	UNIT
Drain-source Voltage	VDS	500	V
gate-source Voltage	VGS	±30	V
Continuous Drain Current(TC=25℃)	ID	13	A
Drain Current-Pulsed	IDM	50	A
Total Dissipation	PD	190	W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55-150	℃
Single Pulse Avalanche Energy	EAS	880	mJ

■ MECHANICAL

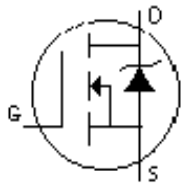


TO-220

1-GATE 栅极

2-DRAIN 漏极

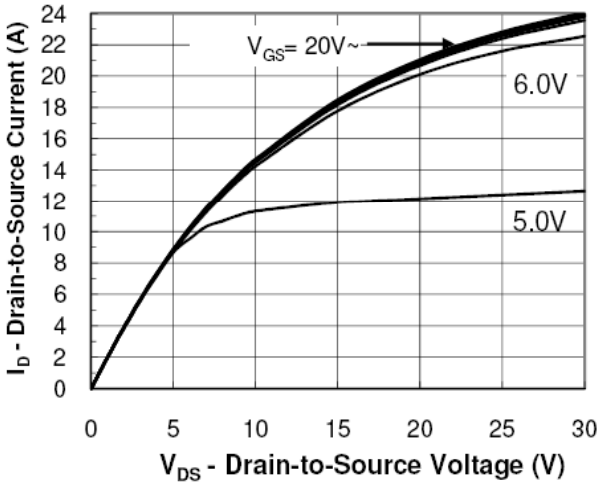
3-SOURCE 源极



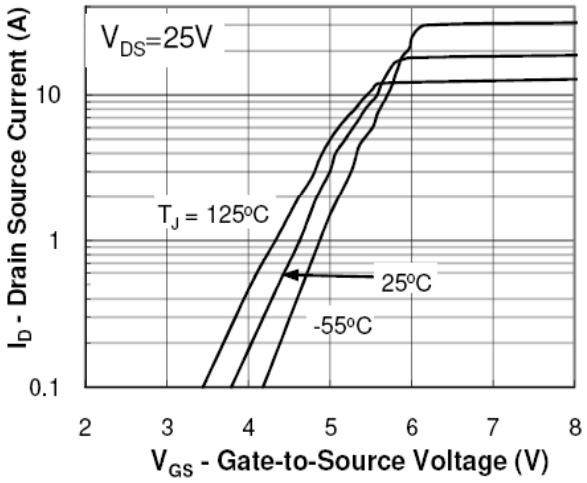
■ ELECTRONIC CHARACTERISTICS (Tc=25℃)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Drain-source Breakdown Voltage	BVDSS	VGS=0V, ID=250μA	500		V
Gate Threshold Voltage	VGS(TH)	VGS=VDS , ID=250μA	2	4.5	V
Drain-source Leakage Current	IDSS	VDS=500V, VGS=0V		1	uA
Drain-Source Diode Forward Voltage	VSD	VGS=0V, IS=13A		1.5	V
Gate-body Leakage Current (VDS = 0)	IGSS	VGS=±30V		±100	nA
Forward Transconductance	gfs	Vds=10V Id=6.5A	6		S
Static Drain-source On Resistance	RDS(ON)	VGS=10V, ID=6.5A		0.48	Ω
Thermal Resistance Junction-case	RthJ-c			2.4	℃/W

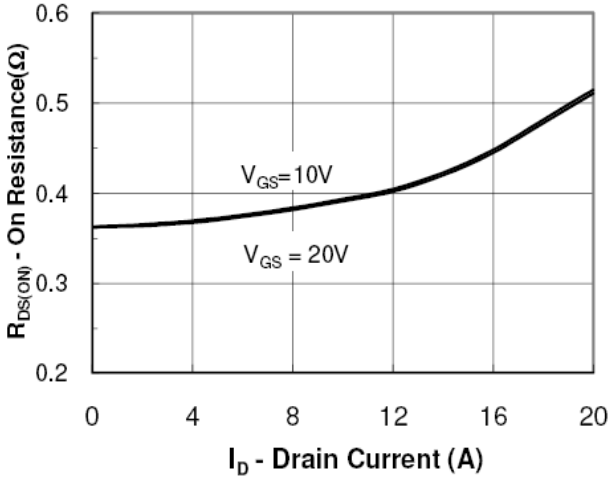
CHARACTERISTICS CURVE



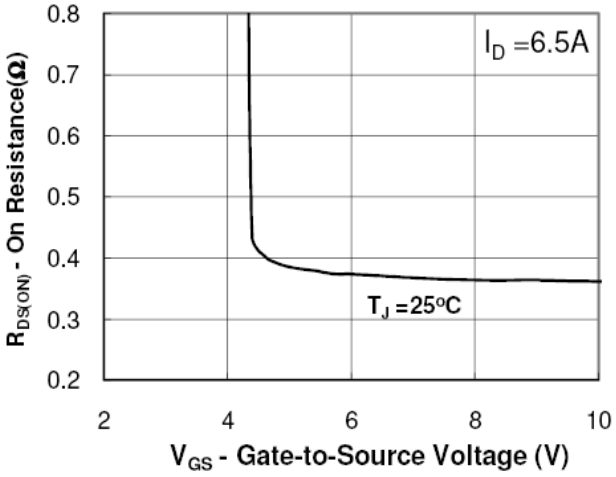
Output Characterisic



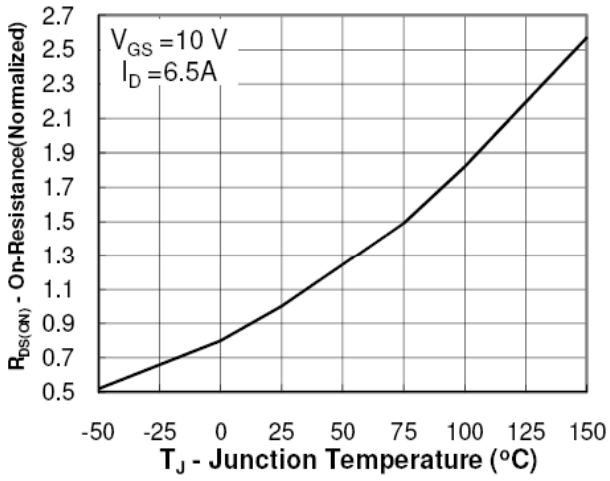
Transfer Characterisic



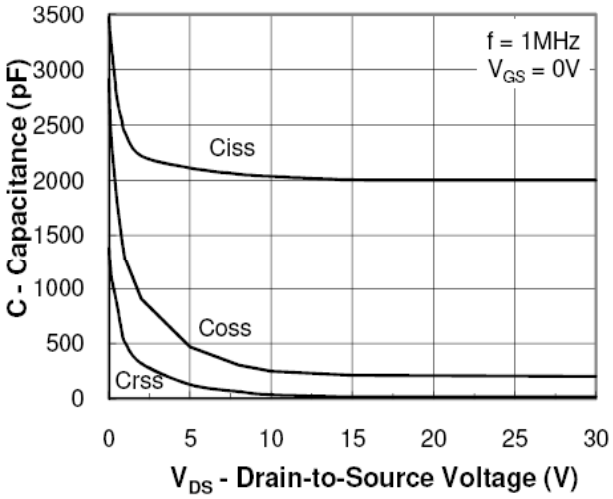
On Resistance Vs Drain Current



On Resistance Vs Gate Source Voltage

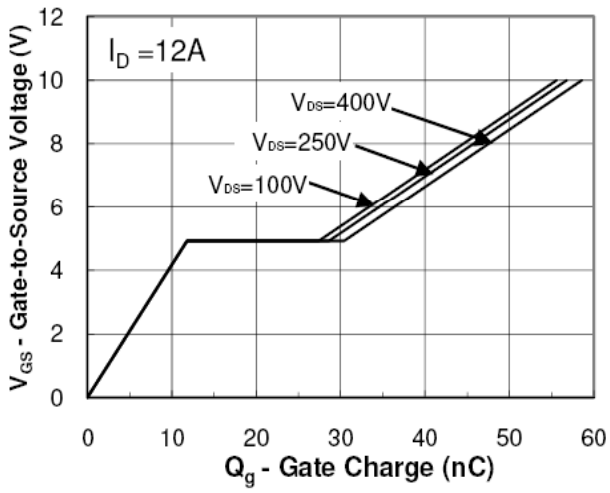


On Resistance Vs Junction Temperature

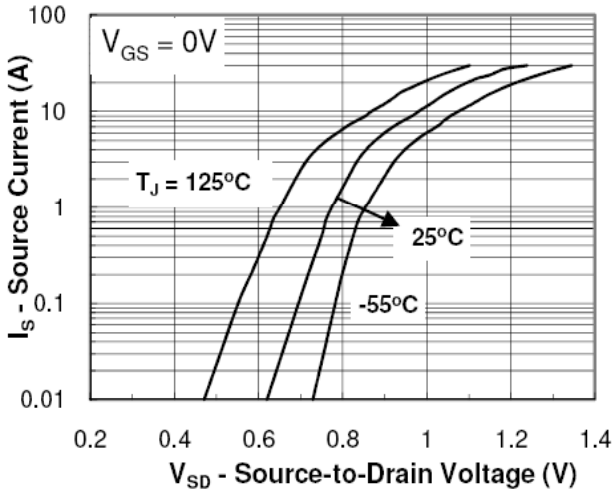


Capacitance

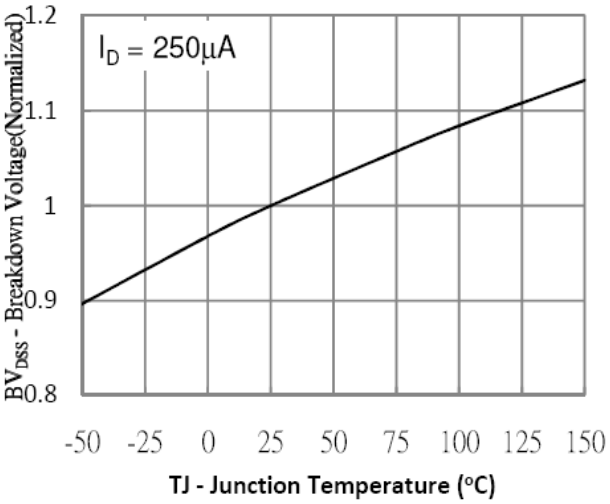
CHARACTERISTICS CURVE



Gate Charge Waveform



Source-Drain Diode Forward Voltage



Breakdown Voltage Vs Junction Temperature

TO-220 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4		4.8	e	2.44	2.54	2.64
B	1.2		1.4	F	1.1		1.4
B1	1		1.4	L	12.5		14.5
b1	0.75		0.95	L1	3	3.5	4
c	0.4		0.55	ΦP	3.7	3.8	3.9
D	15		16.5	Q	2.5		3
D1	5.9		6.9	Q1	2		2.9
E	9.9		10.7